

IDM			
IGBT	49.90%	MOSFET	21.43%
50%	IDM		
	11.5%		
	27.3%	6.63	
		2019	
IDM	44.71%	43.18%	

W

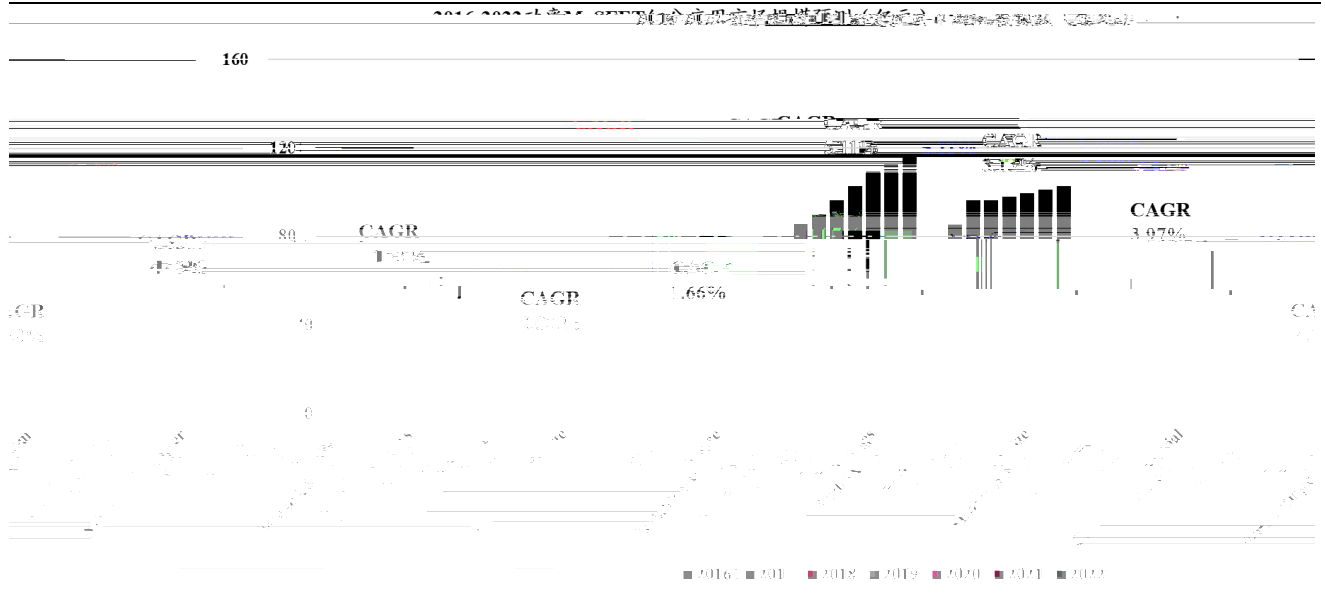
1

同山 (2020年1-9月)						
14.78%	晶圓製造	105984.39	*234508.70	128524.31	109532.49	3.35%

1200V 650V SiC

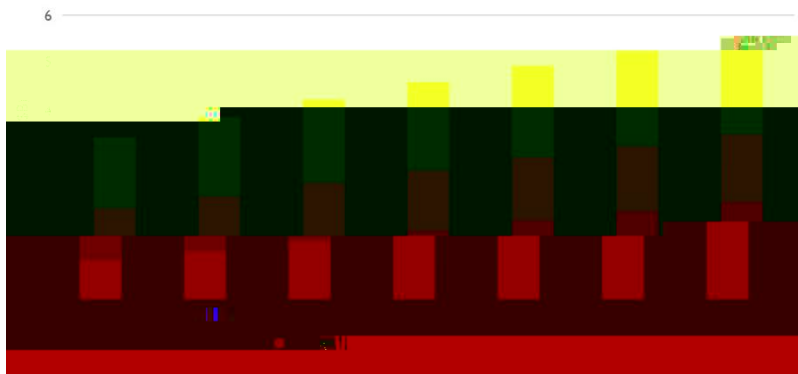
6 SiC

2 MOSFET



Yole

3 IGBT



Yole

20181201201620162017

